

MOS FIELD EFFECT TRANSISTOR **2SJ601**

SWITCHING P-CHANNEL POWER MOS FET INDUSTRIAL USE

| DESCRIPTION | | | ORDERING INFORMATION | | | |
|--|------------------------|--------------|----------------------|---------|----------|--|
| The 2SJ601 is P-channel MOS Field Effect Transistor designed | | | PART NUMBER | | PACKAGE | |
| for solenoid, motor and lamp driver. | | | 2SJ | 601 | TO-251 | |
| FEATURES | | | 2SJ6 | 01-Z | TO-252 | |
| Low on-state resistance: | | | | | | |
| $R_{DS(on)1} = 31 \text{ m}\Omega \text{ MAX.} (V_{GS} = -10 \text{ V}, \text{ In})$ | ο = _18 Δ) | | | | | |
| $R_{DS(on)2} = 46 \text{ m}\Omega \text{ MAX.} (V_{GS} = -4.0 \text{ V}, \text{ m})$ | | | | | | |
| Low Ciss: Ciss = 3300 pF TYP. | 10 - 10 M | | | | | |
| Built-in gate protection diode | | | | | | |
| TO-251/TO-252 package | | | | - | | |
| • 10 201/10 202 package | | | 2. 42 | 15- I'' | | |
| ABSOLUTE MAXIMUM RATINGS (1 | 「 _A = 25°C) | | y on Con | C1. | (TO-251) | |
| Drain to Source Voltage ($V_{GS} = 0 V$) | Vdss | <u>-6</u> 0 | V | | | |
| Gate to Source Voltage (Vgs = 0 V) | Vgss | ∓20 | V | | | |
| Drain Current (DC) (Tc = 25°C) | D(DC) | ∓36 | А | | | |
| Drain Current (pulse) Note1 | D(pulse) | ∓12 0 | А | | | |
| Total Power Dissipation (Tc = 25°C) | Рт | 65 | W | | | |
| Total Power Dissipation ($T_A = 25^{\circ}C$) | Ρτ | 1.0 | W | | (TO-252) | |
| Channel Temperature | Tch | 150 | °C | | | |
| Storage Temperature | Tstg | –55 to +150 | °C | | | |
| Single Avalanche Current Note2 | las | -35 | А | | | |
| Single Avalanche Energy Note2 | Eas | 123 | mJ | | Ø | |

Notes 1. PW \leq 10 μ s, Duty cycle \leq 1%

2. Starting T_{ch} = 25°C, R_G = 25 Ω , V_{GS} = -20 V \rightarrow 0 V

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

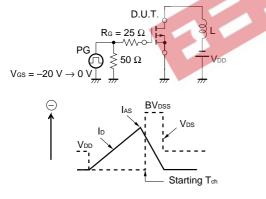
| Characteristics | Symbol | Test Conditions | MIN. | TYP. | MAX. | Unit |
|-------------------------------------|-----------------|---|------|------|------|------|
| Zero Gate Voltage Drain Current | loss | $V_{DS} = -60 V, V_{GS} = 0 V$ | | | -10 | μA |
| Gate Leakage Current | lgss | $V_{GS} = \mp 20 V$, $V_{DS} = 0 V$ | | | ∓10 | μA |
| Gate Cut-off Voltage | VGS(off) | $V_{DS} = -10 V$, $I_D = -1 mA$ | 1.5 | 2.0 | 2.5 | V |
| Forward Transfer Admittance | y _{fs} | $V_{DS} = -10 V$, $I_D = -18 A$ | 15 | 30 | | S |
| Drain to Source On-state Resistance | RDS(on)1 | V _{GS} = -10 V, I _D = -18 A | | 25 | 31 | mΩ |
| | RDS(on)2 | $V_{GS} = -4.0 V$, $I_D = -18 A$ | | 32 | 46 | mΩ |
| Input Capacitance | Ciss | V _{DS} = -10 V | | 3300 | | pF |
| Output Capacitance | Coss | V _{GS} = 0 V | | 580 | | pF |
| Reverse Transfer Capacitance | Crss | f = 1 MHz | | 230 | | pF |
| Turn-on Delay Time | td(on) | $V_{DD} = -30 V$, $I_D = -18 A$ | | 11 | | ns |
| Rise Time | tr | V _{GS(on)} = -10 V | | 12 | | ns |
| Turn-off Delay Time | $t_{d(off)}$ | $R_G = 0 \Omega$ | | 80 | | ns |
| Fall Time | tr | | | 53 | | ns |
| Total Gate Charge | QG | V _{DD} = -48 V | | 63 | | nC |
| Gate to Source Charge | QGS | V _{GS} = -10 V | | 10 | | nC |
| Gate to Drain Charge | Qgd | ID = -36 A | | 16 | | nC |
| Body Diode Forward Voltage | VF(S-D) | IF = -36 A, VGS = 0 V | | 1.0 | | V |
| Reverse Recovery Time | trr | $I_{\rm D} = -36 \text{ A}$ $I_{\rm F} = -36 \text{ A}, \text{ V}_{\rm GS} = 0 \text{ V}$ $I_{\rm F} = -36 \text{ A}, \text{ V}_{\rm GS} = 0 \text{ V}$ $di/dt = -100 \text{ A}/1/\text{s}$ | | 52 | | ns |
| Reverse Recovery Charge | Qrr | di/dt = $-100 \text{ A}/\mu \text{s}$ | | 108 | | nC |



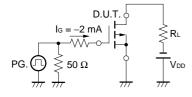
TEST CIRCUIT 2 SWITCHING TIME

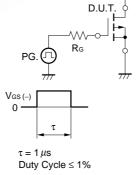
 $\frac{1}{2}$

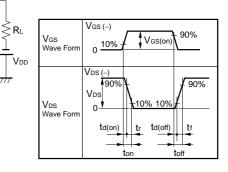
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TEST CIRCUIT 3 GATE CHARGE



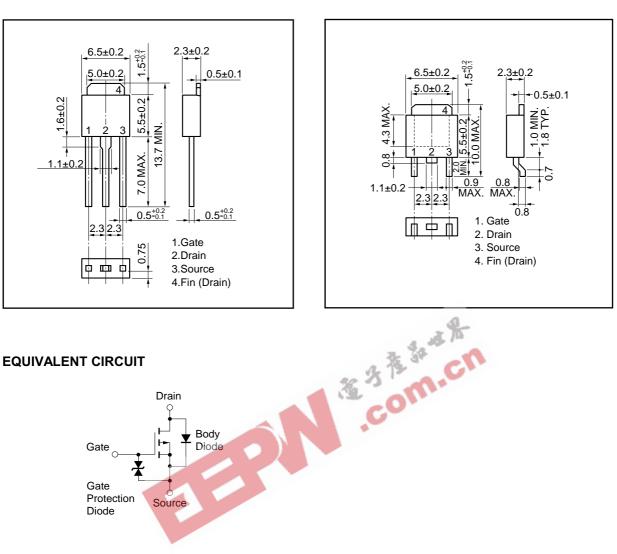




Preliminary Data Sheet D14646EJ1V0DS

PACKAGE DRAWINGS (Unit : mm)

1) TO-251 (MP-3)



2) TO-252 (MP-3Z)

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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